

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((wafer ((semiconductor silicon) near substrate)) with ((3d near (element structure portion)) (connection near (area structure portion))) with protrud\$3 with ((casting near (compound layer material)) ((insulat\$3 dielectric) near layer)) with (redistribution ((conduct\$3 metal) near1 (layer trace pattern))) with expos\$3 with ((separat\$3 near corridor) (scribe near (line region area)))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:02
L2	0	((wafer ((semiconductor silicon) near substrate)) same ((3d near (element structure portion)) (connection near (area structure portion))) same protrud\$3 same ((casting near (compound layer material)) ((insulat\$3 dielectric) near layer)) same (redistribution ((conduct\$3 metal) near1 (layer trace pattern))) same expos\$3 same ((separat\$3 near corridor) (scribe near (line region area)))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:02
L3	0	((wafer ((semiconductor silicon) near substrate)) and ((3d near (element structure portion)) (connection near (area structure portion))) and protrud\$3 and ((casting near (compound layer material)) ((insulat\$3 dielectric) near layer)) and (redistribution ((conduct\$3 metal) near1 (layer trace pattern))) and expos\$3 and ((separat\$3 near corridor) (scribe near (line region area)))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:03
L4	26	(wafer ((semiconductor silicon) near substrate)) and ((3d near (element structure portion)) (connection near (area structure portion))) and protrud\$3 and ((casting near (compound layer material)) ((insulat\$3 dielectric) near layer)) and (redistribution ((conduct\$3 metal) near1 (layer trace pattern))) and expos\$3 and ((separat\$3 near corridor) (scribe near (line region area)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:10

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L5	26	(wafer ((semiconductor silicon) near substrate)) and ((3d near (element structure portion)) (connection near (area structure portion))) and (protrud\$3 protrus\$3) and ((casting near (compound layer material)) ((insulat\$3 dielectric) near layer)) and (redistribution ((conduct\$3 metal) near1 (layer trace pattern))) and expos\$3 and ((separat\$3 near corridor) (scribe near (line region area)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:11
L6	58	(wafer ((semiconductor silicon) near substrate)) and ((3d near (element structure portion)) (connection near (area structure portion))) and (protrud\$3 protrus\$3) and ((casting near (compound layer material)) ((insulat\$3 dielectric) near layer)) and (redistribution ((conduct\$3 metal) near1 (layer trace pattern))) and expos\$3 and ((separat\$3 near corridor) ((scribe recess groove) near (line region area)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:21
L7	32	6 not 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:12
L8	6128	257/e23.021,e23.124.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:15
L9	5290	257/737,773.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:17
L10	4377	438/110,113,115,613,666.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:20

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L11	4010	257/620,622,e21.596,e21.599.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:21
L12	17509	8 9 10 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:21
L13	50	12 and (wafer ((semiconductor silicon) near substrate)) and ((3d near (element structure portion)) ((contact connection) near (area region structure portion))) and (protrud\$3 protrus\$3) and ((casting near (compound layer material)) ((insulat\$3 dielectric) near layer)) and (redistribution ((conduct\$3 metal) near1 (layer trace pattern))) and expos\$3 and ((separat\$3 near corridor) ((scribe recess groove) near (line region area)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:24
L14	35	13 not 5 not 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 10:25
L15	2	("6680536").URPN.	USPAT	OR	ON	2007/09/26 10:27
L16	3	("6221750" "6482013" "6499216").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/26 10:27